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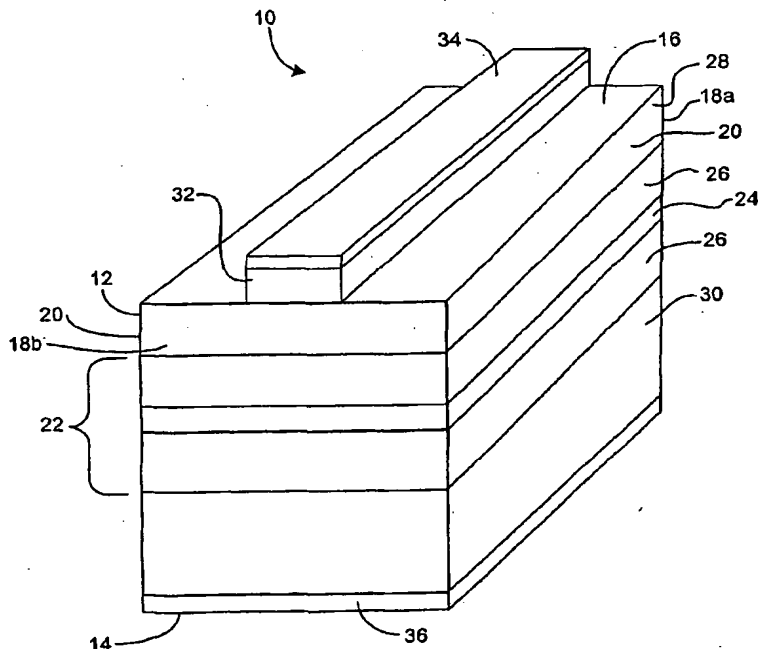
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(54) Title: HIGH-POWER SEMICONDUCTOR LASER



(57) Abstract: A light source includes a semiconductor diode laser, and a reflector having a three-dimensional pattern of refractive index variations within the reflector. The reflector is in optical communication with the semiconductor diode laser and is aligned with an output beam of the diode laser, such that a portion of the light in the output beam is reflected back into the laser by the reflector.

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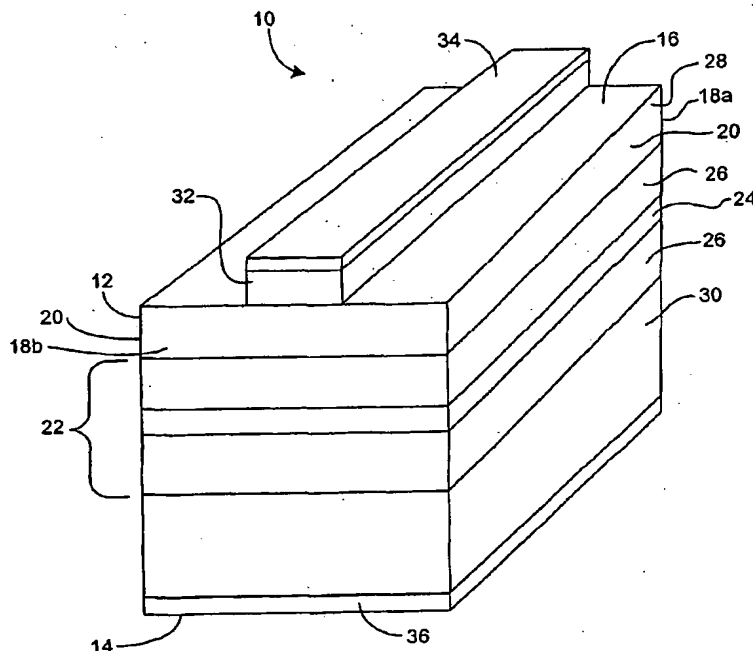
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